providing a semiconductor structure having [the] a base layer, [the] an insulation layer, and [the] a monocrystalline silicon layer;

introducing [the] a passivating substance X [into one of] between the insulation layer and the monocrystalline silicon layer [during or after the fabrication of the semiconductor structure]; and

heat-treating the semiconductor structure with the passivating substance X, thereby causing the passivating substance to diffuse into an interface between the insulation layer and the monocrystalline silicon layer.

Claim 12 (amended). The method according to claim 7, which comprises patterning the monocrystalline silicon layer by etching away regions thereof down to [the] an underlying insulation layer.

Remarks:

Reconsideration of the application is requested.

Claims 1-15 are remain in the application. Claims 7 and 12 have been amended. Claims 1-6 have been withdrawn from consideration.